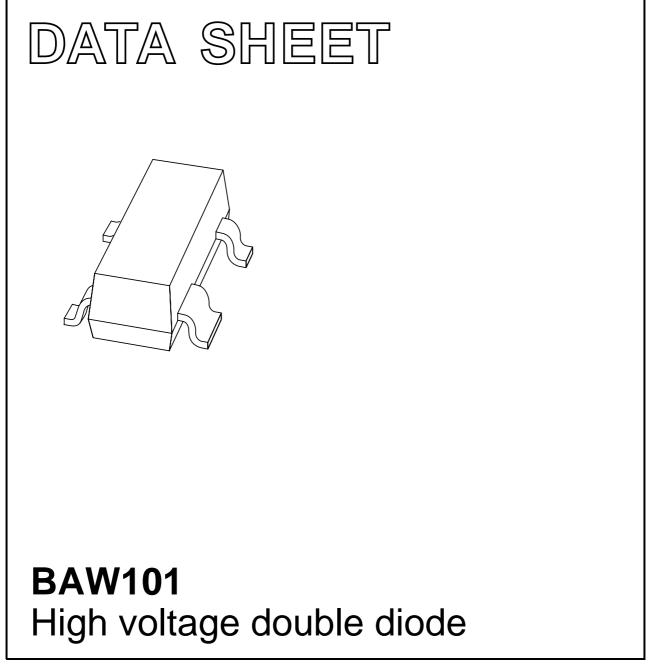
DISCRETE SEMICONDUCTORS



Product data sheet

2003 May 13



FEATURES

- Small plastic SMD package
- High switching speed: max. 50 ns
- High continuous reverse voltage: 300 V
- Electrically insulated diodes.

APPLICATIONS

- High voltage switching
- Automotive
- Communication.

DESCRIPTION

The BAW101 is a high-speed switching diode array with two separate dice, fabricated in planar technology and encapsulated in a small SOT143B plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	
BAW101	*AB	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION	
1	cathode 1	
2	cathode 2	
3	anode 2	
4	anode 1	

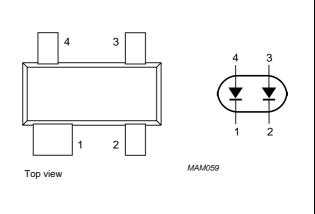


Fig.1 Simplified outline (SOT143B) and symbol.

BAW101

BAW101

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode			•		
V _R	continuous reverse voltage		_	300	V
		series connection	_	600	V
V _{RRM}	repetitive peak reverse voltage		-	300	V
		series connection	_	600	V
I _F	continuous forward current	single diode loaded; note 1; see Fig.2	_	250	mA
		double diode loaded; note 1; see Fig.2	-	140	mA
I _{FRM}	repetitive peak forward current		_	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; $T_j = 25 \text{ °C}$ prior to surge; t = 1 µs	-	4.5	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	350	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on an FR4 printed-circuit board, cathode-lead mounting pad = 1 cm^2 .

ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per diode	Per diode					
V _{BR(R)}	reverse breakdown voltage	I _R = 100 μA	300	_	V	
V _F	forward voltage	I _F = 100 mA; note 1	-	1.1	V	
I _R	reverse current	V _R = 250 V	-	150	nA	
		V _R = 250 V; T _{amb} = 150 °C	-	50	μA	
t _{rr}	reverse recovery time	when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$; measured at $I_R = 3$ mA	_	50	ns	
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	-	2	pF	

Note

1. Pulse test: pulse width = 300 μ s; δ = 0.02.

BAW101

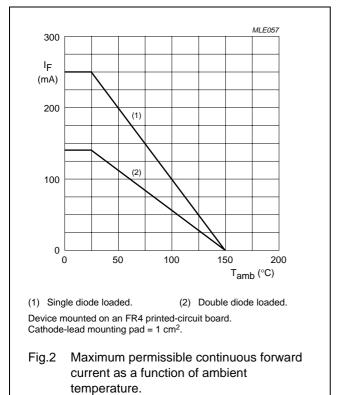
THERMAL CHARACTERISTICS

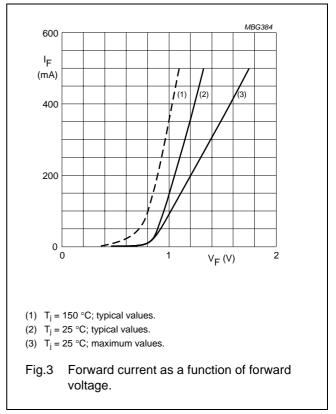
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	note 1	255	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 2	357	K/W

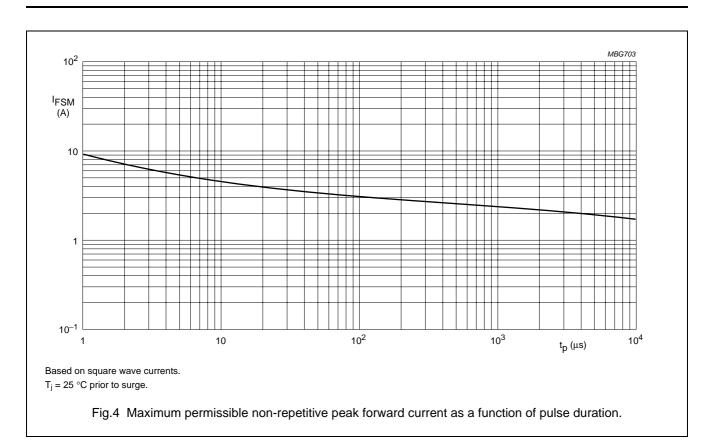
Notes

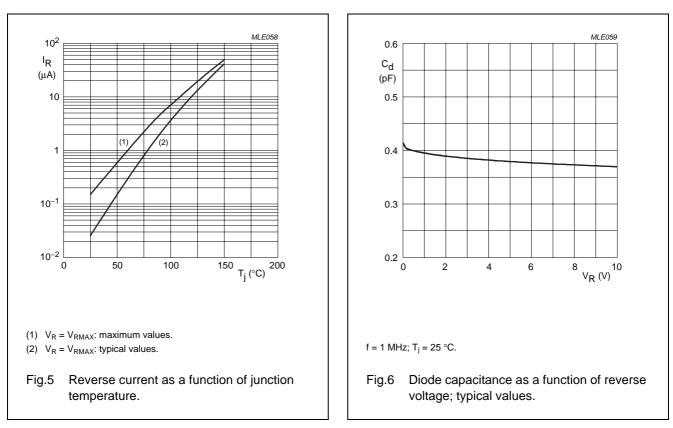
- 1. One or more diodes loaded.
- 2. Device mounted on an FR4 printed-circuit board, cathode-lead mounting pad = 1 cm^2 .

GRAPHICAL DATA









BAW101

MLE060 400 V_{R} (V) 300 200 100 0 0 50 100 150 200 T_{amb} (°C) Fig.7 Maximum permissible continuous reverse voltage as a function of ambient temperature.

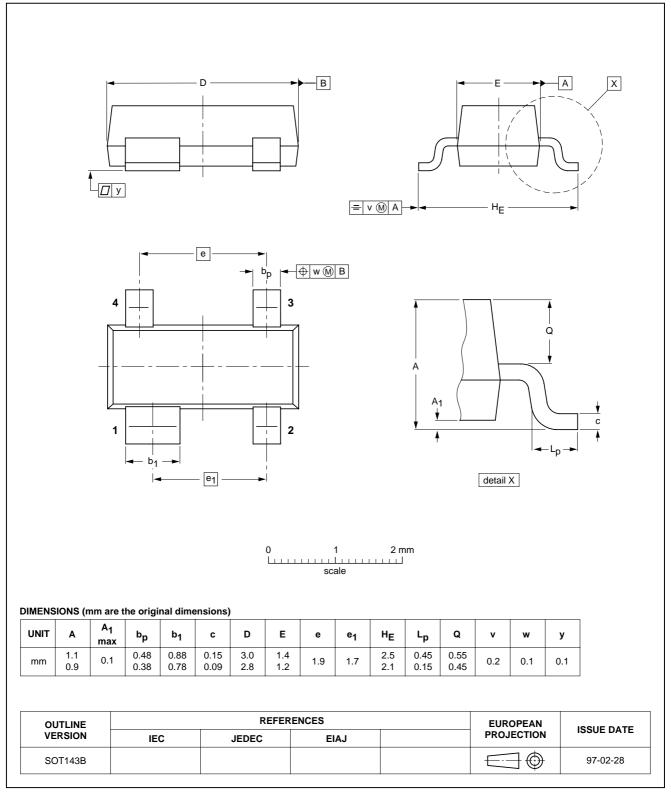
BAW101

Product data sheet

High voltage double diode

PACKAGE OUTLINE





SOT143B

BAW101

DATA SHE	ET STATUS
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DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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